arXiv:1305.0031v1 [cond-mat.dis-nn] 30 Apr 2013

Nonlinearity exponents in disordered systems

K. K. Bardhan[1] and D. Talukdar[2]
[1]*Kalpana Chawla Centre for Space and Nano Sciences, 3F Swamiji Nagar, Kolkata 700 030, India**
[2]*Saha Institute of Nuclear Physics, I/AF Bidhannagar, Kolkata 700 064, India*

(Dated: May 2, 2013)

The effect of an electric field on conduction in a disordered system is an old but largely unsolved problem. Experiments cover an wide variety of systems - amorphous/doped semiconductors, conducting polymers, organic crystals, manganites, composites, metallic alloys, double perovskites - ranging from strongly localized systems to weakly localized ones, from strongly correlated ones to weakly correlated ones. Theories have singularly failed to predict any universal trend resulting in separate theories for separate systems. Here we discuss a recent one-parameter scaling that has been found to give a systematic account of the field-dependent conductance in two strongly localized systems of conducting polymers and manganites. The nonlinearity exponent, x associated with the scaling was unexpectedly found to possess multiple values. We find that the scaling applies to all other systems as mentioned. For 3D strongly localized systems the exponent lies between -1 and 1, and surprisingly, is quantized ($x \approx 0.08\ n$). For 2D weakly localized systems, the nonlinearity exponent $\boldsymbol{x}$ is $\geqslant 9$ and is roughly inversely proportional to the sheet resistance. Existing theories of weak localization prove to be adequate in explaining the proposed scaling which however poses a challenge for theories in case of strong localization.

PACS numbers: 66.30.Pa, 62.20.Dc, 81.07.–b

I. INTRODUCTION

Effects of disorder on transport phenomena have been studied for more than four decades[1], yet understanding is still far from complete. One of the effects of disorder is to drive samples into nonOhmic regime even under small bias. This effect is particularly pronounced in small-sized samples such as nanodevices. It is thus necessary to understand the phenomena of nonlinear transport to ensure that the devices operate as desired with optimum properties. In seventies the focus was on the materials such as amorphous/doped semiconductors which are recognized today as strongly localized systems characterized by the exponential dependence of conductivity on temperature. The conduction occurs through variable range hopping (VRH) between randomly occurring localized states. The theories[1–3] proved inadequate to account for the experimental data in the full range of applied field (see below and Ref. [4] for a recent critique). Subsequently, new disordered regimes, namely weak localization in 2D and metal-insulator transition (MIT) in 3D were identified by Abrahams et al.[5]. The experiments[6] were mostly limited to verification of the prediction[7] of logarithmic variation in weak localization of conductivity with either temperature at small bias or large bias at low temperature. Here we attempt to find a universal description of the response to an applied electric field by adopting a model-independent scaling approach. The strong motivation comes from the remarkable similarity in the response of different disordered regimes in diverse materials such as mentioned earlier. In this approach the quantity which is of major interest is the field scale (or the onset field), F_o at which a sample deviates from the Ohmic behavior. It is shown that while the scaling formally is same across the regimes the associated exponent x varies and is nonuniversal. In 2D weak localized regimes, the exponent x is roughly inversely proportional to the sheet resistance. It becomes quantized in strong localization. The current theories of weak localization and region around the MIT support the scaling. This makes the scaling quite plausible in strong localization which however remains a theoretical challenge. All discussion here are limited to two and three dimensions only.

II. SCALING OF FIELD-DEPENDENT CONDUCTANCE

The field-dependent conductance can be written in general as $\Sigma(M, F) = \Sigma_o(M)\ \Phi(F, M)$ where F is the field and M stands for the control parameter (most commonly, temperature) which is varied to change the linear conductance $\Sigma_o(M) = \Sigma(M, 0)$. Following the spirit of the scaling theory[5] we assume that Φ is a function of F and $\Sigma_o(M)$ only and not of temperature or size explicitly. This is also motivated by the goal to have quenched disorder (corresponding to samples fabricated under different conditions) as a valid parameter for M. Thus, $\Sigma(M, F) = \Sigma_o(M)\ \Phi(F, \Sigma_o(M))$. It is natural to expect that Φ will be a function of F/F_o. Hence the scaling that the disordered systems are expected to follow is given by[4,8]

$$\frac{\Sigma(M, F)}{\Sigma_o(M)} = \Phi\left(\frac{F}{F_o}\right). \tag{1}$$

In analogy to power-laws in critical phenomena we have

$$F_o(M) \sim \Sigma_o(M)^{x_M}, \tag{2}$$

where the 'critical' conductance is zero for all cases. x_M is the nonlinearity exponent with a subscript for the control parameter. The above relation allows seamless consideration of disorder as the control parameter (see Fig. 6b of Ref. 4 for an illustration). A lower bound of x_M may be obtained by considering the current scale $I_o \sim \Sigma_o F_o \sim {\Sigma_o}^{x+1}$. Since I_o should remain finite when Σ_o is very small this obtains $x \geqslant -1$. At small $q(=F/F_o) \leqslant 1$, $\Phi(q) \approx 1$. At large field ($q \gg 1$), the conductance often becomes independent of T (or, $\Sigma_o(T)$) (see Fig. 1) when the control parameter is temperature. It is seen from Eq. (1) and (2) that this requirement is readily ensured if $\Phi(q) \sim q^{1/x_T}$ at large q for $x_T > 0$. Thus, at large fields the conductivity varies as a power-law, $\Sigma(T,F) \sim F^{z_T}$ such that for $x_T > 0$

$$z_T = 1/x_T. \tag{3}$$

The above relation can be understood by simply writing the conductance as $\Sigma \approx \Sigma_o + bF^{1/x_T}$ where b is a constant. This immediately generates $F_o \sim {\Sigma_o}^{x_T}$. Note that the similar scaling (Eqs. 1-3) with F and F_o replaced by the frequency and its characteristic value[9] also describes the ac-conductivity at different ac amplitudes.

A. Weak localization

We first discuss nonlinear conduction in 2D weakly localized thin films by revisiting the data of Dolan and Osheroff[6] shown in the inset (a) of Fig. 1. The data contain a lot more information than the simply logarithmic variation with the applied field. Indeed, the sample resistance $R(=1/\Sigma)$ with an initial Ohmic value (R_o) looks similar to those in strongly localized systems[4]. Clearly, there exists a voltage scale $V_o(T)$ at each T such that $R \approx R_o$ for $q(=V/V_o) \leqslant 1$ and R decreases for $q > 1$. As shown in Fig. 1 (main panel), the collapse of all data at various temperatures on a single curve[10] confirms the universality of the scaling in Eq. (1). Here $V_o(T)$ is chosen such that $R(T,V_o) = (1+\epsilon)R_o(T)$ with $\epsilon = -0.05$. The solid line in Fig. 1 indicates a power-law at large fields, $R \sim V^{z_T}$ where the exponent z_T is 1/64.9. The inset (b) displays a log-log plot of V_o vs. R_o which yields a large value[11] for the nonlinearity exponent $x_T = 64.9 \pm 0.4$ fulfilling the requirement $z_T \approx 1/x_T$ (Eq. 2). At large fields the resistance variation in weak scattering regime is given by the hot electron model[6,7]

$$\frac{R(T,V)}{(1+\epsilon)R_o(T)} - 1 = -R_\square \Sigma_u \lambda_V \ln\left(\frac{V}{V_o}\right), \tag{4}$$

where $R_\square$ is the temperature-independent sheet resistance, $\Sigma_u = e^2/2\pi^2\hbar = 1.2 \times 10^{-5}\ \Omega^{-1}$, $\lambda_V = \alpha p/(1+p/2)$, and α an universal constant. The exponent p is defined by $\tau_{in} \sim T^{-p}$ where τ_{in} is the inelastic relaxation time. The above expression is compatible with Eq. (1). Considering that the change in R is small, the above can be recast as a power-law $R/R_o = (1+\epsilon)(V/V_o)^{z_T}$ with the exponent $z_T = R_\square \Sigma_u \lambda_V$. With $R_\square = 4600\ \Omega$ and $\lambda_V = 0.28$ (Ref. 6), one determines $z_T = 1/62.9$ which is close to $1/64.9$ obtained from the digitized data (Fig. 1). To obtain x_T from the hot electron model[7] we consider the relevant energy balance relation[12]:

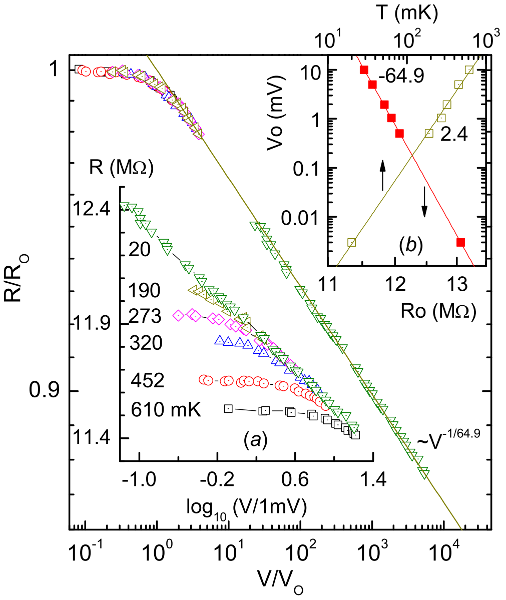


FIG. 1. Scaling in 2D weakly localized metallic thin films of AuPd. Plots of resistance vs. electric bias at different temperatures are shown in the inset (a) (data adapted from Ref. 6). Scaling of the same data leads to the data collapse as shown in the main panel. $R_o(T)$ and $V_o(T)$ are the Ohmic resistance and the onset bias respectively at temperature T. Inset (b) shows log-log plots of V_o vs. R_o (solid symbols) and T (open symbols). The solid lines are linear fits to the data with the slopes as mentioned.

$$\sigma_o F^2 \tau_{in}(T_e) \sim {T_e}^2, \tag{5}$$

where T_e is the effective electron temperature and σ_o is the temperature-independent Ohmic conductivity. At the onset of nonlinearity $T_e \sim T$ so that

$$F_o \sim T^{1+p/2}. \tag{6}$$

The above provides the most direct method for determining p. A plot of F_o vs. T in the inset (b) yields $1 + p/2 \approx 2.4$ close to 2.6 reported in Ref. (6). A similar expression as in Eq. (4) can be written for temperature at small bias leading to $R_o \sim T^{-R_\square \Sigma_u \alpha p}$. Using this in Eq. (6) gives Eq. (2) with $x_T = 1/R_\square \Sigma_u \lambda_V = 1/z_T$. With λ_V being of the order of unity, $x_T \approx 81000/R_\square \gg 1$ since the maximum metallic sheet resistance is predicted to be about 30 kΩ[6]. Thus, the exponent in the 2D metallic state should have the minimum value $x_T^{min} \approx 3$.

To verify that $x_T \propto 1/R_\square$, exponents (open symbols) processed from the data available in literature for four different materials (films) of thicknesses 3-13 nm are shown in Fig. 2. All data are seen to lie on a line

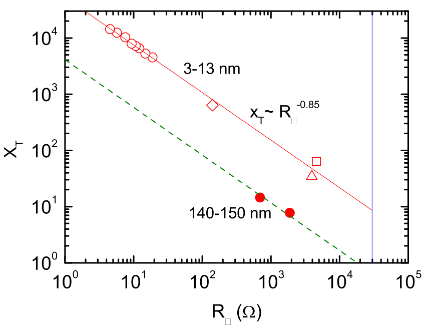


FIG. 2. Effect of film thickness on the nonlinearity exponent in 2D metallic states. The exponent is plotted against sheet resistance for various materials and film thicknesses. One set of data (open symbols) belongs to thin films (□-AuPd [6], △-Pt[13], ⋄-Au[12]), and ○-Cu[14]). Another set of data (closed symbols) is from thick films (Refs. 15). The solid line is a least square fit and the dashed line is drawn parallel to it. The vertical line corresponds to the maximum metallic resistance of 30 kΩ.

with a slope of -0.85 which is close to the expected value of -1. The small discrepancy may be due to the variation in experimental p. Also shown in the figure are the data (closed circles) from two thick films[15] ($\mathrm{Ge}_{0.79}\mathrm{Au}_{0.21}$ and $\mathrm{C_xCu_{1-x}}$ of thickness 140-150 nm near, but on the metallic side of, the metal-insulator transition in 3D[5]). These thick films appear to be in the cross-over regime from 2D to 3D. The reported small temperature variation of conductivities ($\sim T^{0.02-0.07}$) is akin to the logarithmic one characteristic of a 2D system. A film is supposed to be 2D if the inelastic mean free path l_ϕ is greater than the thickness. Using an alternative of Eq (5), $eF_o l_\phi \sim kT$ and $F_o \approx 9$ V/cm at 1.5 K, we estimate $l_\phi \sim 160$ nm i.e. of the order of film thickness. While these data from thick films separately follow the same trend with sheet resistance as thin films, the exponents are roughly an order of magnitude less than those in thin films for similar sheet resistances. This trend in the exponent value is in agreement with the experimental results in 3D strongly localized systems where x_T decreases to a value less than 1 (see Tables in Appendix B and below). p determined from the onset field data using Eq. (6) is 0.9 and 0.7 for the two films respectively. These results indicate a possible renormalization of the constant α with the film thickness. The fitted line yields $x_T^{min} \sim 9$.

B. Metal-Insulator transition (MIT)

We now consider a regime[16,17] somewhat intermediate between weak localization with the logarithmic dependence, and strong localization with the activated exponential dependence, of the Ohmic conductivity σ_o. Such a regime occurs in the vicinity of the MIT with large localization length[5]. The conduction takes place through hopping of electrons across the localization centers. The conductivity has a power-law dependence on temperature[17], $\sigma_o \sim T^{p/3}$ in contrast to the exponential variation, $\ln\sigma_o \sim -(T_o/T)^m$. Here T_o is a characteristic temperature and the exponent m can vary from 1/4 (variable range hopping or VRH) to 1 (nearest neighbor hopping)[1]. Usually, $T_o \gg T$. However when $T_o \leqslant T$, the average hopping length is of the order of the localization length and the exponential form is replaced by a power-law. In the case where T is the control parameter, we apply the hot electron model (Eq 5) as before and use $\sigma_o \sim T^{p/3}$ to obtain $z_T = 1/(1+p/3)$ and $x_T = 1 + p/3 = 1/z_T$ (Eq. 3). With $p \sim 1$, x_T is predicted to be about 1.3. Rosenbaum et al.[18] measured field-dependent conductivity in Si:P samples near but on the insulating side of, the MIT at different temperatures. The behavior of $\sigma_o(T)$ was rather ambiguous. Nevertheless, the data were found to obey the scaling (Eq. 1) to give $x_T = 0.15 \pm 0.01$ (Appendix A). While $\sigma_o(T)$ yielded an unphysically large $p \approx 30$, $F_o(T)$ yielded $p \approx 1$ (Eq. 6) indicating that the hot electron model perhaps may not be applicable in this regime. Clearly, the experimental exponent (< 1) does not match the predicted value (> 1) but the value is compatible with the ones found in strong localized systems (see below).

C. Strong localization

The diverse strongly localized systems as mentioned in the beginning are described by the universal scaling as in Eq. (1). However a much desired theoretical framework which would be independent of the microscopic details as in 2D is missing at present. Instead, there exist separate theories for separate systems[1–3] , often falling short of fulfilling the general requirements of the model-independent scaling. For example, the existing literature[1–3] on VRH-type transport deals with two field scales. The recent study[4] has clearly established the fact that there exists only *one* field scale, not two and the scale is not simply related to either of the two length scales - the average hopping length and the localization length (see also Ref. 18). The same is observed in other VRH classes such as amorphous/doped semiconductors[19], composites at low temperature[19] whose data are available in literature.

As a further example of implications of the model-independent scaling, let us discuss a non-VRH, correlated system, namely layered organic crystals θ-(BEDT-TTF)$_2$CsZn(SCN)$_4$ by examining the experimental data and the proposed model[20]. Disorder arises out of random presence of holes in the charge-ordered layers. The low field transport in the insulating phase of these crystals is characterized by an activated process with m=1, T_o=24 K. The I-V characteristics were measured at different temperatures and found to follow the power-

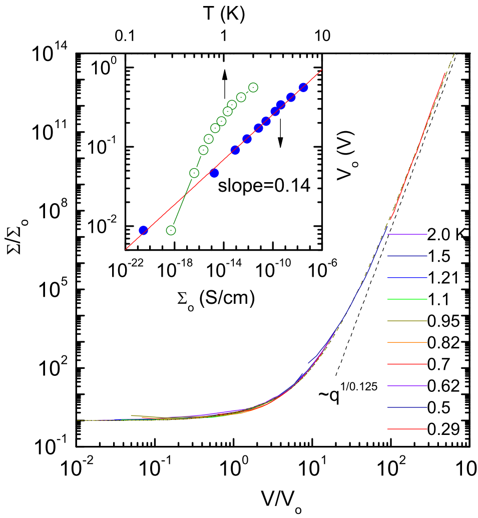


FIG. 3. Scaling of the bias-dependent conductance data in a correlated, charge-ordered organic salt at different temperatures. The original I-V data are taken from Ref. 20. The voltage scale V_o is chosen corresponding to $\Sigma(V_o) = 2\Sigma_o$. The solid line is a fit to the scaled version of Glazman-Matveev expression[4]: $\Sigma/\Sigma_o = 1 + 0.97q^{4/3} + 0.0025q^{14/3} + 1.5 \times 10^{-8}q^{70/9}$ ($q = V/V_o$). Inset shows two log-log plots of V_o vs. Σ_o (closed symbols) and T (open symbols). The solid line is a linear fit to the data (closed symbols) with the slope as shown.

law at large bias with a large exponent (~ 8.4) similar to observations in many systems including conducting polymers[4], a-Ge[21] or a-Si:H[22]. Authors suggested a model based on unbinding of electron-hole pairs by thermal excitation in the background of the charge-ordered ground state. The power-law characteristics was given by $I \sim V^{1\ +U_o/2kT}$ so that $z_T = U_o/2kT$. Furthermore, the onset (or, crossover) field was given by the temperature-independent $F_o = U_o/e\lambda$ implying $x_T = 0$. Here U_o is the strength of the Coulomb potential and λ is the screening length. Thus, according to the model $x_T \neq 1/z_T$. Experimental data adapted from[20] and normalized according to Eq. (1) are presented in Fig. 3. The high quality of the collapse of the data at various temperatures points toward validity of the scaling to this correlated system. Here ϵ was 1 for determining V_o. Ohmic conductances at lower T were obtained from extrapolation of the data at higher T. The scaled data in the figure represent essentially the scaling function Φ. The inset shows plots of V_o vs. Σ_o and T. The straight line through the closed circles proves the validity of Eq. (2) (over a conductance range of 14 decades!) and yields a non-zero exponent $x_T = 0.14 \pm 0.01$ in contradiction with the model prediction. Also shown in the figure is a dashed line parallel to the scaled curve at high bias and having a slope of 1/0.125 close to 1/0.14 as expected according to Eq. (3). λ was determined using F_o. The inset in Fig. 3 shows that F_o increases with temperature. Consequently, λ must decrease with temperature. Therefore, this casts doubt on the conclusion (i.e., the long-ranged Coulomb interaction) drawn from a particular value of F_o. The model expression of a temperature-dependent z_T is untenable, particularly at low T or/and at high fields when the conductivity becomes temperature-independent i.e., 'activationless'. If hopping is considered then the conductivity is given by $\sigma \approx \exp(-2r_h/\xi)$ where r_h is the hopping length and ξ is the localization length. Using $r_h = U_o/eF$ corresponding to the logarithmic potential one gets $\ln\sigma \sim -2U_o/eF\xi$, an exponential rather than power-law dependence. Similar predicament also arises in VRH[2]. We note that for a slightly different potential well $U = U_o[1-\exp(-r/\lambda)]$ the energy minimization leads to $r = \lambda\ln(U_o/eF\lambda)$ yielding a power-law dependence, $\sigma \approx (F/F_o)^{z_T}$ where $F_o = U_o/e\lambda$ and $z_T = 2\lambda/\xi$.

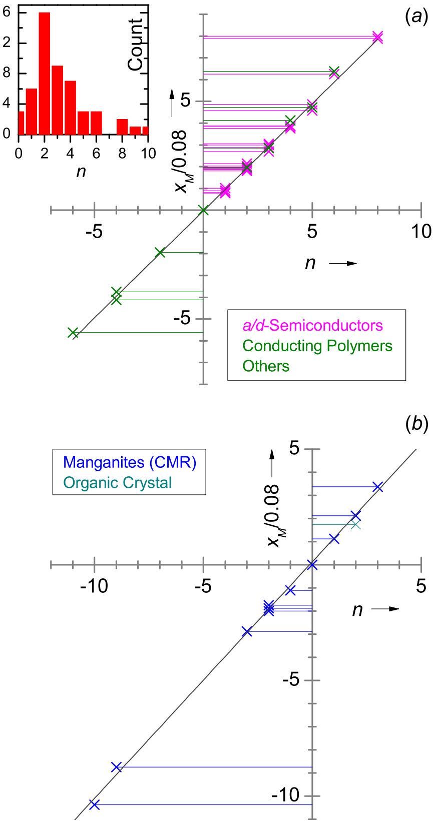


FIG. 4. The nonlinearity exponents x_M in several (a) uncorrelated and (b) correlated classes of materials. The exponents are quantized and given by $x_M \approx 0.08n$. This is highlighted by plotting $x_M/0.08$ against n with lines dropped off the data points to y-axes. Each panel shows a solid line passing through the origin with a slope of unity. The inset in panel (a) displays the histogram of the exponents in the same panel.

Comparison of the insets in Figs. 1 and 3 highlights the difference in behavior of $V_o(T)$ in weak and strong localization respectively. Similarly, the huge difference in the ranges of y-axes of Figs. 1 and 3 illustrates the effects of x_T being greater and less than 1. A puzzling fact however is that the scaled curve could be nicely fitted by a modified Glazman-Matveev expression[4] requiring only three powers.

III. DISCUSSION

Values of the nonlinearity exponent extracted in this work from various 3D strongly localized systems reported in literature are given in Table I (Appendix B). Exponents in conducting polymers and manganites already reported in Refs.[4,8] are shown for convenience in Tables II and III. It is quite apparent from the tables that in stark contrast to thermodynamic critical phenomena, the universal scaling lacks an universal exponent. Recall that in 2D weak localization $x_T \propto 1/R_\square$. In 3D strong localization one notices the large spread in values of the nonlinearity exponent not only in different systems but also in the *same* material. For example, the five different samples of a-Ge examined had for the exponent two values of 0.16 and three values of ∼0.24 (Table I). No correlation seems to exist between x_T and $T_o(10^7\text{K})$: (0.16, 8), (0.16, 8.9), (0.24, 0.5), (0.23, 2.6), and (0.24, 1) respectively. In doped polypyrrole, there are exponents with even different signs, i.e., 0.23 and -0.33. However, all values so far lie within the bounds, -1 and +1. On a closer inspection of the exponents in the Tables we observe a remarkable fact that an exponent, positive or negative, could be described as an integer multiple of a number ≈ 0.08 i.e., $x_M \approx 0.08n$ where n is an integer which can take both positive and negative values including zero. The number, 0.08 is thus the largest common factor among the exponents in the tables. To highlight the quantized nature of the exponents, $x_M/0.08$ is plotted against n for weakly- or non-correlated materials in Fig. 4a, and for correlated materials in Fig. 4b with lines dropped off the data symbols to y-axes. The solid line in each figure is a line with a slope of unity and passing through the origin. Points are seen to be lying close to the lines confirming the quantized behavior and distinct bands form around integer values on the y-axis. The width and density of a band reflect the spread in the values, and the frequency, respectively of the associated exponent found in the systems examined so far. The fact that the exponents follow the same relation in both correlated and uncorrelated systems makes an impressive statement on the new universal physics at play in the field-dependent conduction in strongly disordered systems.

Some points are in order. i) The inset in Fig. 4a shows a histogram of the exponents in the panel (a). The distribution exhibits a pronounced peak at n=2 and is clearly asymmetric around the peak with a tail towards large n. ii) Both conducting polymers and amorphous/doped semiconductors follow VRH-type transport. Yet, the exponents in the former assume both positive and negative values whereas those in the latter assume only positive values; iii) For $x_M = 0$, the field-dependence and temperature-dependence of conductance becomes completely separate (Eq. 1); iv) The field scales remain unaffected by an applied magnetic field i.e. $x_B = 0$ (Tables I and II). Although a magnetic field does not impart any energy to electrons the zero value of x_B is still significant because a magnetic field destroys time reversal invariance and is known to influence a wavefunction. However, in 2D weak localized regime Eq (5) predicts a negative exponent, $x_B = -0.5$. There is yet no experimental confirmation of this prediction ; v) For disorder as a control parameter, x_D in polpyrrole was found to be negative, -0.33. Interestingly, Eq (5) does yield a negative exponent, $x_D = -0.5$. On the other hand, Larkin et al.[16] discussed a model of the MIT regime that yields a positive exponent, $x_D = 1 + \eta$ where the exponent η relates the energy scale with length scale; vi) Limited data (x_D, x_B) indicate that x_M follows the same quantized behavior even when M is not temperature.

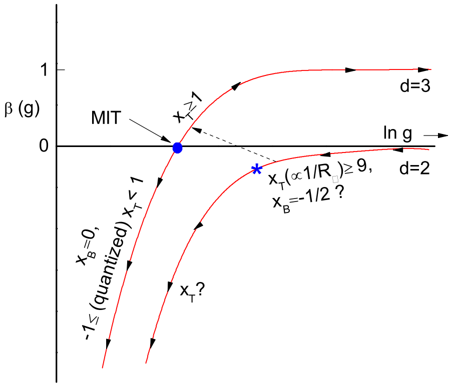


FIG. 5. Summary of the nonlinearity exponent in various regimes in the T=0 scaling diagram with same axes[5]. The solid point representing the metal-insulator transition (MIT) is predicted to have an another one in x_T. The star (corresponding to $R_\square \approx 30\text{k}\Omega$) represents the zone that separates the metallic and insulating states on the 2D curve. The dashed line schematically denotes cross-over from 2D to 3D with increase of thickness. '?' denotes experimentally either unavailable or unverified information.

Fig. 5 summarizes the experimental findings about the nonlinearity exponent in disordered systems in 2D and 3D on the T=0 scaling diagram[5]. For highly conducting 3D samples, the nonlinear exponent is undefined. As the MIT is approached from the metallic side, $x_T > 1$[15]. As MIT is just crossed to the insulating side, $x_T < 1$[18]. Therefore, the MIT is also the point where x_T appears to undergo a sharp transition in value from one > 1 to one < 1. However confirmation about the transition must await further experimental as well as theoretical input. For large conductance in 2D, the exponent $x_T \geqslant\sim 9$. Information about x_T at larger disorder is lacking. But if it is found to have values < 1 as in 3D, an intriguing question arises: does the point (star) on the 2D curve corresponding to $R_\square \approx 30\text{k}\Omega$ represent simply a crossover zone or a transition manifest only in the nonlinear regime? The dashed line represents schematically a possible path corresponding to increasing thickness of a 2D film when the exponent decreases from a large value to one closer to 1 as discussed earlier (Fig. 2).

In summary, heuristic arguments were presented for a universal one parameter scaling of field-dependent conductance in 2D and 3D disordered systems, supported by abundant experimental evidence. The associated exponent possesses a spectrum of values characteristic of various disordered regimes. The unexpected quantization of the exponent in strong localization points toward a new physics and calls for further theoretical efforts. A possible transition in 2D is speculated and several unresolved issues are discussed. It is apparent that the electric field along with the traditional magnetic field should be valuable probes for transport in disordered systems.

ACKNOWLEDGMENTS

Authors thankfully acknowledge discussions with Upen Nandi, Chandidas Mukherjee, Asok Sen and Bikas Chakrabarti. They also acknowledge help provided by Upen Nandi and Biswajit Das in processing some data.

---

[*] kamalk.bardhan@saha.ac.in

[1] N. F. Mott and E. A. Davis, *Electron Processes in Non-crystalline Materials, 2nd ed.* (Clarendon Press, Oxford, 1979).

[2] B. I. Shklovskii, Sov. Phys. Semicond., **10**, 855 (1976).

[3] M. Pollak and I. Riess, J. Phys. C: Solid State Phys., **9**, 2339 (1976).

[4] D. Talukdar, U. N. Nandi, K. K. Bardhan, C. C. Bufon, T. Heinzel, A. De, and C. D. Mukherjee, Phys. Rev. B, **84**, 054205 (2011).

[5] E. Abrahams, P. W. Anderson, D. C. Licciardello, and T. V. Ramakrishnan, Phys. Rev. Lett., **42**, 673 (1979).

[6] G. J. Dolan and D. D. Osheroff, Phys. Rev. Lett., **43**, 721 (1979).

[7] P. W. Anderson, E. Abrahams, and T. V. Ramakrishnan, Phys. Rev. Lett., **43**, 718 (1979).

[8] D. Talukdar, U. N. Nandi, and K. K. Bardhan, Phys. Rev. B, **86**, 165104 (2012).

[9] K. K. Bardhan and R. K. Chakrabarty, Phys.Rev. Lett, **69**, 2559 (1992).

[10] (), the values of R_o at T=20 and 190 mK were obtained from extrapolation of Fig. 2 of Ref. 6.

[11] (), such a large value usually indicates an exponential variation. However, we stick with the power-law to maintain continuity with rest of the discussion.

[12] S. I. Dorozhkin and V. T. Dolgopolov, Zh. Eksp. Teor. Fiz. Lett., **36**, 15 (1982), [JETP Lett. 36, 18 (1982)].

[13] H. Hoffmann, F. Hofmann, and W. Schoepe, Phys. Rev. B, **25**, 5563 (1982).

[14] L. Van den dries, C. Van Haesendonck, and Y. Bruynseraede, Phys. Rev. Lett., **46**, 565 (1981). We assumed p=2. x_T was then determined from the slope of $\ln T$ by dividing it by $1+p/2$ and ranged from 4500 (62Å) to 14300 (130Å).

[15] M. Osofsky et al., Phys. Rev. B, **38**, 8486 (1988); **38**, 12215 (1988). The data obey the scaling in Eq. (1) with x_T = 7.8 and 14.5 for Ge$_{0.79}$Au$_{0.21}$ and C$_x$Cu$_{1-x}$ respectively (unpublished).

[16] A. I. Larkin and D. E. Khmel'nitskii, Zh. Eksp. Teor. Fiz., **83**, 1140 (1982), [Sov. Phys. JETP 56, 647 (1982)].

[17] Y. Imry, J. Appl. Phys., **52**, 1817 (1981).

[18] T. F. Rosenbaum, K. Andres, and G. A. Thomas, Solid State Comm., **35**, 663 (1980).

[19] D. Talukder, U. N. Nandi, C. D. Mukherjee, and K. K. Bardhan, Unpublished.

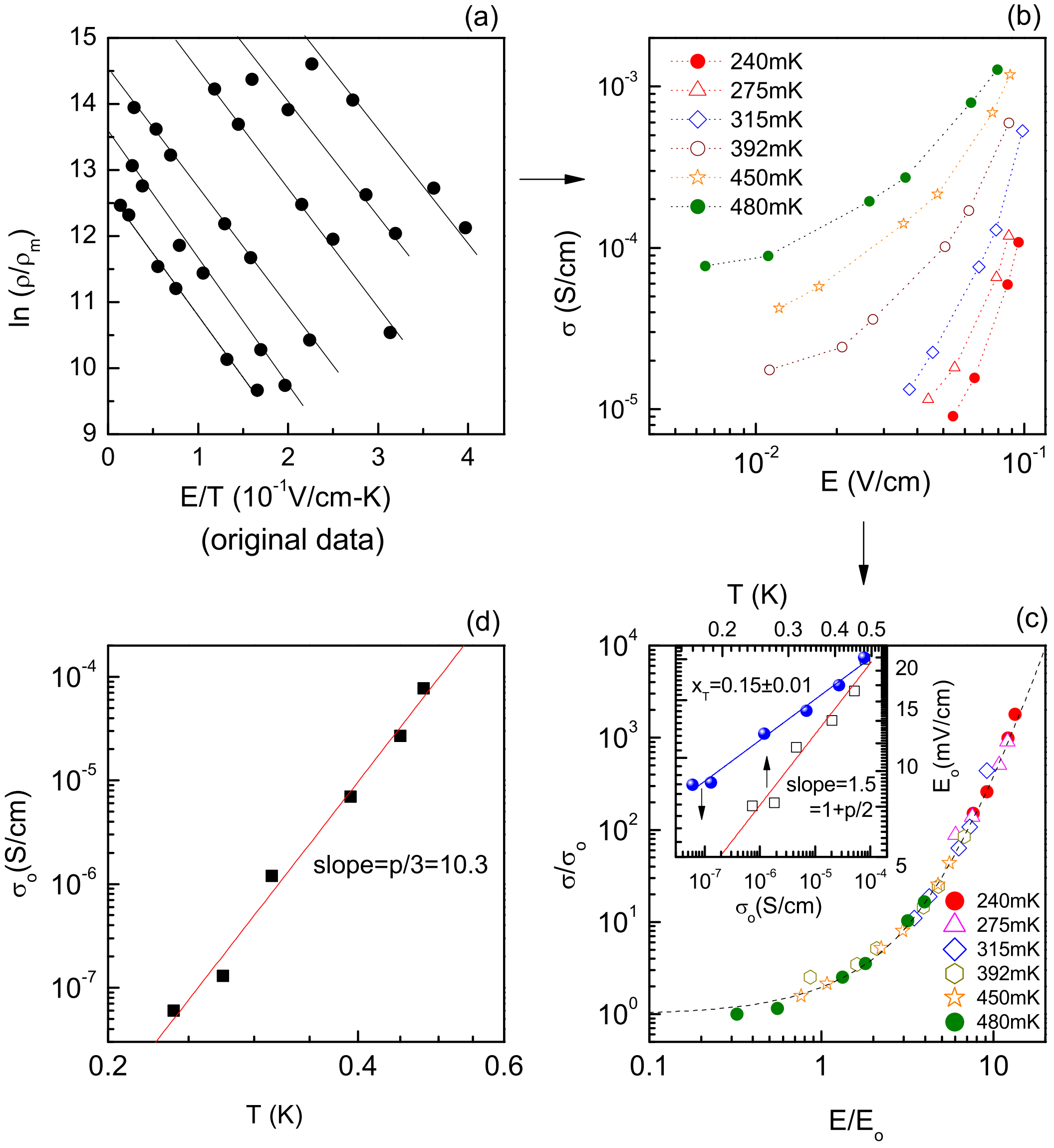
[20] Y. Takahide, T. Konoike, K. Enomoto, M. Nishimura, T. Terashima, S. Uji, and H. M. Yamamoto, Phys. Rev. Lett., **96**, 136602 (2006).

[21] M. Morgan and P. A. Walley, Phil. Mag., **23**, 661 (1971).

[22] C. E. Nebel, R. A. Street, N. M. Johnson, and C. C. Tsai, Phys. Rev. B, **46**, 6803 (1992).

Appendix A: Data of Rosenbaum et al.

Appendix B: Tables



Scaling of I-V data of Rosenbaum et al. Solid State Comm., 35, 663 (1980).

FIG. 6.

TABLE I. The nonlinearity exponents x_M for different materials (mostly exhibiting variable range hopping) obtained using the scaling formalism. T,D and B represent temperature, disorder and magnetic field respectively as the control parameter. Data sources are shown. m is the VRH exponent and n is the quantization integer.)

Systems	m	x_T	x_B	n	Data Source
a-Semicond.					
a-Si:Y	0.5	0.063		1	F Ladieu et al., Phys Rev B 61, 8108 (2000)
a-Si:H		0.065		1	C E Nebel et al., Phys Rev B 46, 6803 (1992)
a-SiO	0.25	0.072		1	A Servini et al.,Thin Sol Films 3, 341(1969)
a-CN:H	0.25	0.16		2	S Kumar et al., J Non-Cryst Solids 338-340,349 (2004)
a-Ge	0.25	0.155		2	M Morgan et al., Phil Mag, 23, 661 (1971)
a-Ge	0.25	0.16		2	M Telnic et al., Phys Stat Solidi(b) 59, 699 (1973)
a-Ge	0.25	0.244		3	P J Elliot et al., AIP Conf. Proc. 20, 311 (1974)
a-Ge	0.25	0.23		3	T Suzuki et al., J Non-Cryst Solids 23, 1 (1977)
a-Ge	0.25	0.24		3	N Croitoru et al., Thin Sol Films 3, 269 (1969)
a-Ge:Cu	0.5	0.37		5	A N Aleshin et al., Sov Phys Semicond. 21, 466(1987)
Doped-semicond.					
n-Si:As	0.5	0.081		1	C Gang et al., Solid State Comm 72, 173 (1989)
n-Si:P	0.25	0.15		2	T N Rosenbaum et al., Solid State Comm 35, 663 (1980)
n-Si:Mn	0.5	0.15		2	A V Dvurechenskii et al., JETP Lett. 48, 155 (1988)
n-GaAs	0.5	0.17		2	F Tremblay et al., Phys Rev B 40, 3387 (1989)
n-CdSe	0.5	0.16		2	D Yu et al., Phys Rev Lett 92, 216802 (2004)
n-Si:As	0.25	0.30		4	R W van der Heijden et al., Phil Mag B 65, 849 (1992)
p-Si:B	0.25	0.22		3	Y M Shwarts et al., Sem Phy, Quan Elec Opto 3, 400 (2000)
n-GaAs	0.5	0.31		4	D Redfield, Adv Phys 24, 463 (1975)
n-ZnSe	0.5	0.31		4	I N Timchenko et al., Sov Phys Semicond. 23, 240 (1989)
d-Ge:Ga	0.5	0.5		6	T W Kenny et al., Phys Rev B 39, 8476 (1989)
n-Si:P	0.5	0.64		8	J Zhang et al., Phys Rev B 57, 4472 (1998)
Composite					
SCNT-PMMA	0.5	0.39		5	J M Benoit et al., Phys Rev B 65, 241405 (2002)
C-PVC	0.67	0.63		8	L J Adriaanse et al., Synth Metals 84, 871 (1997)
Double perovskite					
Ba_2MnReO_6	0.5	0.155		2	B Fisher et al., J Appl Phys 104, 033716 (2008)
Organic crystal					
θ-$(BEDT\text{-}TTF)_2$ $CsZn(SCN)_4$	1	0.14		2	Takahide et al., Phys Rev Lett 96, 136602 (2006)
θ-$(BEDT\text{-}TTF)_2$ $CsZn(SCN)_4$	1		0	0	Takahide et al., Phys Rev Lett 96, 136602 (2006)

TABLE II. The nonlinearity exponents for different conducting polymers from Phys. Rev. B 84, 054205(2011).

System	m	x_T	x_D	x_B	n
PPy (powder)	0.25	-0.329±0.014			-4
PPy (film)	0.33	-0.155±0.012			-2
PPy (film)	0.5	-0.228±0.008			3
PPy (film)	-		-0.3		4
PPy (film)	-			0	0
PEDOT	0.5	-.158±0.003			2
PDA	-	-0.51±0.02			6
PA(nanofiber)	-	-0.33±0.02			4

TABLE III. The nonlinearity exponents for CMR phases in different maanganites from Phys. Rev. B 86, 165104 (2012). PI and FM represents the paramagnetic insulating and ferromagnetic phases.

System	x_T^{FM}	n^{FM}	x_T^{PI}	n^{PI}
$Sm_{0.55}(Sr_{0.5}Ca_{0.5})_{0.45}MnO_3$(sc)			0	0
$Sm_{0.55}Sr_{0.3375}Ca_{0.1125}MnO_3$	0.17 ± 0.01	2	0.09 ± 0.01	1
$Sm_{0.55}Sr_{0.45}MnO_3$	-0.23 ± 0.01	-3	-0.14 ± 0.01	-2
$La_{0.275}Pr_{0.35}Ca_{0.375}MnO_3$	-0.09 ± 0.01	-1	0	0
$La_{0.87}(Mn_2O_3)_{0.13}MnO_3$	-0.83 ± 0.01	-10	-0.16 ± 0.01	-2
$La_{0.75}Ca_{0.25}MnO_3$	0.27 ± 0.04	3	0.27 ± 0.04	3
$La_{0.75}Ca_{0.25}MnO_3/BaTiO_3$	-0.70 ± 0.01	-9	-0.15 ± 0.03	-2